i i	Hits	Search Text	DB	Time stamp
umber		117/9.ccls. and amorphous same (silicon	USPAT;	2002/12/17
	78	11//9.ccis. and amorphous same (2222	US-PGPUB;	15:19
		or germanium or si or ge or sige)	EPO; JPO;	
			DERWENT;	
			-	
			IBM_TDB	2002/12/17
ì	5.2	117/9.ccls. and amorphous same (silicon	USPAT;	
	32	or germanium or si or ge or sige) same	US-PGPUB;	15:28
		(heat adj treat\$4 or rapid adj thermal or	EPO; JPO;	
		rta or rtp or ptp or anneal\$4 or laser)	DERWENT;	
		rta or rtp or ptp of annealy of fabout	IBM TDB	
		· · · · · · · · · · · · · · · · · · ·	USPAT;	2002/12/17
_	8	117/9.ccls. and amorphous same (germanium	US-PGPUB;	15:43
		lam do or side) same (heat ad) treating or	EPO; JPO;	10.10
		rapid adj thermal or rta or rtp or ptp or		
		anneal\$4 or laser)	DERWENT;	
			IBM_TDB	0000 (10 /27
	0.4	117/4-9.ccls. and amorphous same	USPAT;	2002/12/17
-	24	(germanium or ge or sige) same (heat adj	US-PGPUB;	15:56
		(germanium of ge of sige) same (most day	EPO; JPO;	
		treat\$4 or rapid adj thermal or rta or	DERWENT;	
		rtp or ptp or anneal\$4 or laser)	IBM TDB	
				2002/12/17
-	42	(117/4-9.ccls. and amorphous near4	USPAT;	
	12	(gilicon or si) same (heat add treat)4 or	US-PGPUB;	16:08
		I manid add thermal or rta or rtp or pup of	EPO; JPO;	
	1	anneal\$4 or laser)) and (ge or germanium)	DERWENT;	
		anneals4 of taseff) and (ge of germanical)	IBM TDB	
			USPAT;	2002/12/17
-	24	(117/4-9.ccls. and amorphous near4	US-PGPUB;	16:48
		(silicon or si) same (laser)) and (ge or	*	1 - 5 - 2 - 2
		germanium)	EPO; JPO;	1
		3	DERWENT;	
			IBM_TDB	
		// manhaus mann3 (silicon or si) and	USPAT;	2002/12/17
-	1	((amorphous near3 (silicon or si) and	US-PGPUB;	17:56
		I I I I I I I I I I I I I I I I I I I	EPO; JPO;	
		sige)) same (anneal\$4 or laser) and IF1)	DERWENT;	
		and 117/\$4.ccls.		
			IBM_TDB	2002/12/18
-	1 ~	(ge or germanium or sige or silicon adj	USPAT;	
	1	germanium) same second near3 amorphous	US-PGPUB;	11:23
		germanitum, same second TET	EPO; JPO;	
		near2 layer and TFT	DERWENT;	
			IBM_TDB	
			USPAT;	2002/12/18
	43	crystal\$4 same second near3 amorphous	US-PGPUB;	11:55
	1	near2 layer and TFT		1
	1	1.000	EPO; JPO;	1
			DERWENT;	
]			IBM_TDB	
		144 mams second near3 amorphous	USPAT;	2002/12/18
_		crystal\$4 same second near3 amorphous	US-PGPUB;	13:16
-		near2 layer and TFT and first near3 (ge	EPO; JPO;	1
		or germanium)	DERWENT;	
			IBM TDB	
		· ·		2002/12/18
		3 TFT and first near3 (ge or germanium)	USPAT;	
	1	3 TFT and first hears (ge of gormans	US-PGPUB;	13:18
		same crystal\$4	EPO; JPO;	1
			DERWENT;	
			IBM TDB	
			USPAT;	2002/12/18
-		7 TFT and first near3 (ge or germanium)		•
		same amorphous	US-PGPUB;	
		Same amorphous	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		, 1 +44 come emerchelle	USPAT;	2002/12/18
-	2	5 electrode same insulat\$4 same amorphous	US-PGPUB;	45 45
		same germanium and TFT	EPO; JPO;	
			DERWENT;	
1	i		IBM TDB	

	161	TFT same anneal\$4 same laser same (xenon	USPAT;	2002/12/18
-	16	or mercury or metal adj halide)	US-PGPUB;	15:20
1		or mercury or metal adj naride,	EPO; JPO;	
		1	DERWENT;	
			IBM TDB	
		- A - A - A - A - A - A - A - A - A - A	USPAT;	2002/12/18
-	40	anneal\$4 same laser same (mercury or	US-PGPUB;	15:25
		metal adj halide)	EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
			USPAT;	2002/12/19
_	39	crystal\$4 near3 improv\$3 same amorphous	US-PGPUB;	09:40
		near5 (silicon or germanium or si or ge		09.40
		or sige) same TFT	EPO; JPO;	
		· ·	DERWENT;	
			IBM_TDB	2002/12/19
-	1	crystal\$4 near3 improv\$3 same amorphous	USPAT;	2002/12/18
	_	near5 (germanium or ge or sige) and TFT	US-PGPUB;	15:49
	1	Titato (germania)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
		crystal\$4 near3 improv\$3 same (germanium	USPAT;	2002/12/18
	24	Crystal 4 Hears Improves Same (9	US-PGPUB;	16:15
		or ge or sige) and TFT	EPO; JPO;	
			DERWENT;	l .
			IBM TDB	
		o (ilimom om gi) same	USPAT;	2002/12/18
	110	amorphous near3 (silicon or si) same	US-PGPUB;	16:23
		plasma adj (CVD or chemical adj vapor adj	EPO; JPO;	
		deposit\$4) and turbo adj molecular adj	DERWENT;	
		pump\$4	IBM TDB	
		and the same	USPAT;	2002/12/18
_	10	amorphous near3 (silicon or si) same	US-PGPUB;	16:35
		lalama adi (CVD or Chemical adi Vapor ad)	EPO; JPO;	
		deposit\$4) same turbo adj molecular adj	DERWENT;	
		pump\$4	IBM TDB	
1		1-	USPAT;	2002/12/18
	1 7	amorphous same silicon same two adj step		16:49
	1 '	same crystal\$4 same laser and tft	US-PGPUB;	10.32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/12/19
	10	amorphous same two adj step same	USPAT;	2002/12/19
_	10	crystal\$4 same laser and tft	US-PGPUB;	09:40
		CLASCATAL Same 10007 min	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	1.0 (1.0
		second near5 anneal\$4 same laser and	USPAT;	2002/12/18
_	79	second nears anneary same ruser and	US-PGPUB;	17:45
		crystal\$4 near5 laser and tft	EPO; JPO;	
			DERWENT;	
1			IBM TDB	[